

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOS)

2SK3761

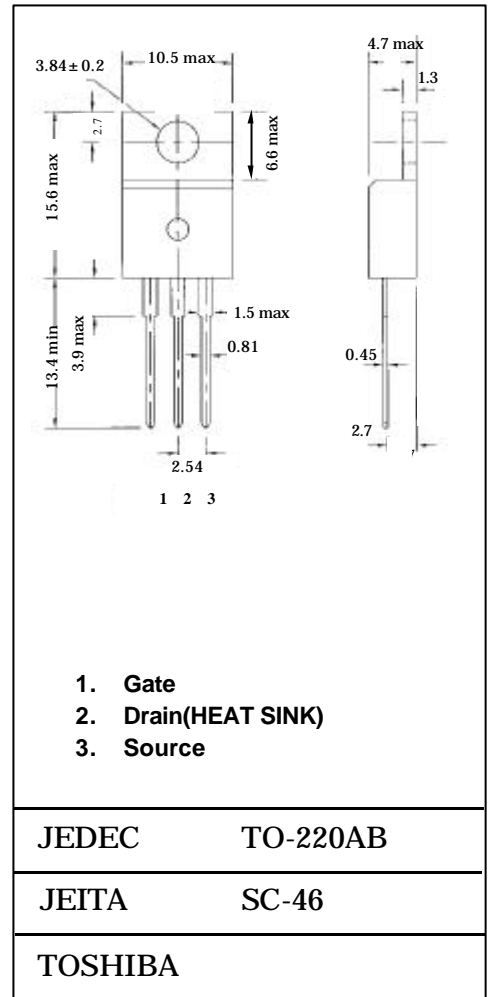
unit : mm

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 0.9$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 5.0S$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu A$ ($V_{DS} = 600 V$)
- Enhancement-mode: $V_{th} = 2.0 \sim 4.0 V$ ($V_{DS} = 10 V, I_D = 1 mA$)

Maximum Ratings ($T_a = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	600	V
Drain-gate voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	600	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	6	A
	Pulse ($t = 1 ms$) (Note 1)	I_{DP}	24	
Drain power dissipation ($T_c = 25^\circ C$)		P_D	74	W
Single pulse avalanche energy (Note 2)		E_{AS}	54	mJ
Avalanche current		I_{AR}	6	A
Repetitive avalanche energy (Note 3)		E_{AR}	7.4	mJ
Channel temperature		T_{ch}	150	$^\circ C$
Storage temperature range		T_{stg}	-55~150	$^\circ C$



Thermal Characteristics

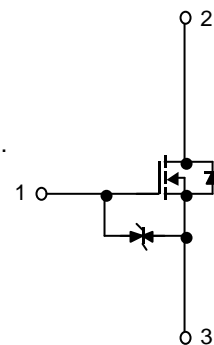
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.68	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	83.3	$^\circ C/W$

Note 1: Please use devices on conditions that the channel temperature is below $150^\circ C$.

Note 2: $V_{DD} = 90 V, T_{ch} = 25^\circ C$ (initial), $L = 2.6 mH, I_{AR} = 6 A, R_G = 25 \Omega$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



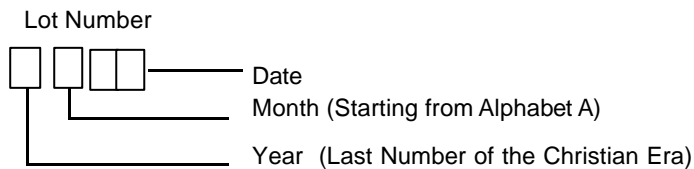
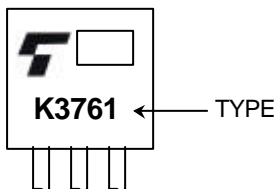
Electrical Characteristics (Ta = 25°C)

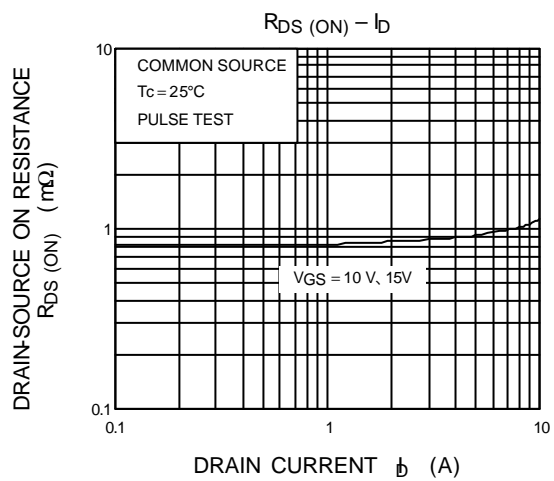
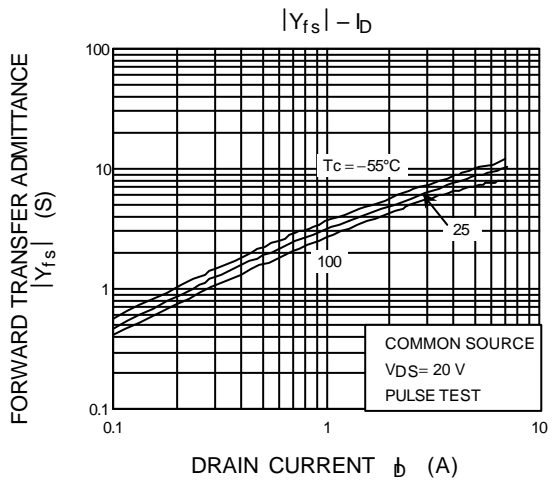
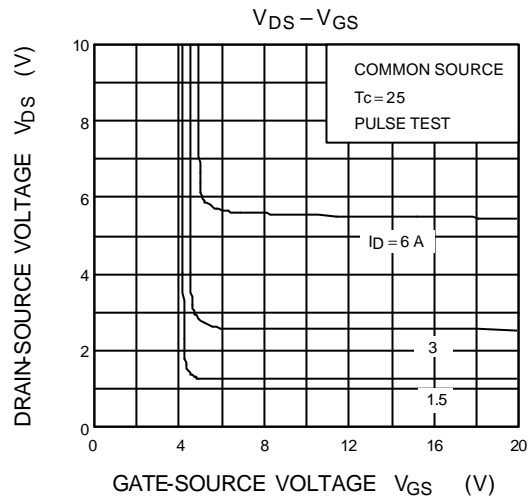
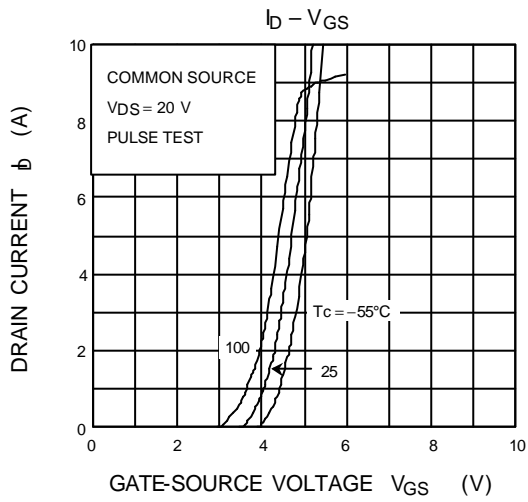
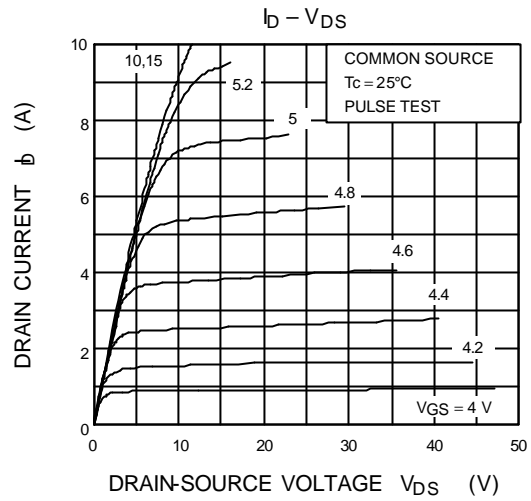
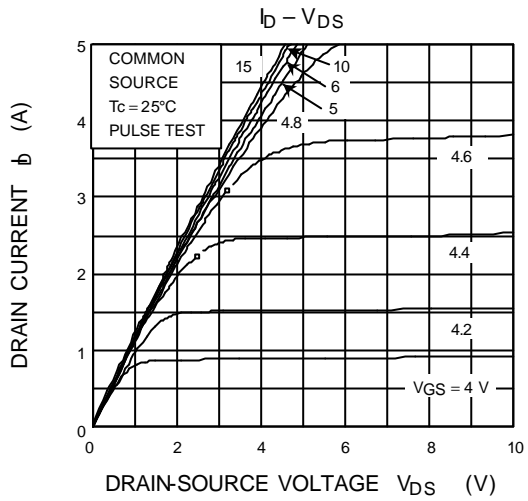
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 V, V_{DS} = 0 V$	—	—	± 10	μA
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_D = \pm 10 \mu A, V_{GS} = 0 V$	± 30	—	—	V
Drain cut-off current		I_{DSS}	$V_{DS} = 600 V, V_{GS} = 0 V$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 mA, V_{GS} = 0 V$	600	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 V, I_D = 1 mA$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 V, I_D = 3 A$	—	0.9	1.25	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 V, I_D = 3 A$	1.2	5.0	—	S
Input capacitance		C_{iss}	$V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz$	—	1050	—	pF
Reverse transfer capacitance		C_{rss}		—	10	—	
Output capacitance		C_{oss}		—	110	—	
Switching time	Rise time	t_r	<p>$V_{GS} = 10 V, 0 V$ $I_D = 3 A$ V_{OUT} 50Ω $R_L = 66 \Omega$ $V_{DD} = 200 V$</p>	—	20	—	ns
	Turn-on time	t_{on}		—	40	—	
	Fall time	t_f		—	35	—	
	Turn-off time	t_{off}		Duty $\leq 1\%, t_w = 10 \mu s$	—	130	
Total gate charge		Q_g	$V_{DD} = 400 V, V_{GS} = 10 V, I_D = 6 A$	—	28	—	nC
Gate-source charge		Q_{gs}		—	16	—	
Gate-drain charge		Q_{gd}		—	12	—	

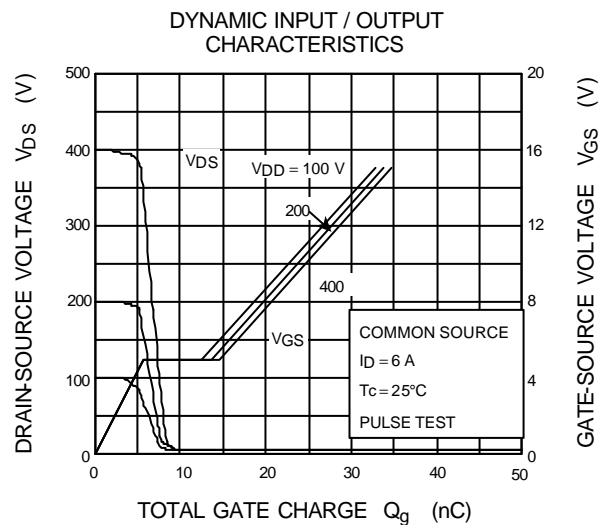
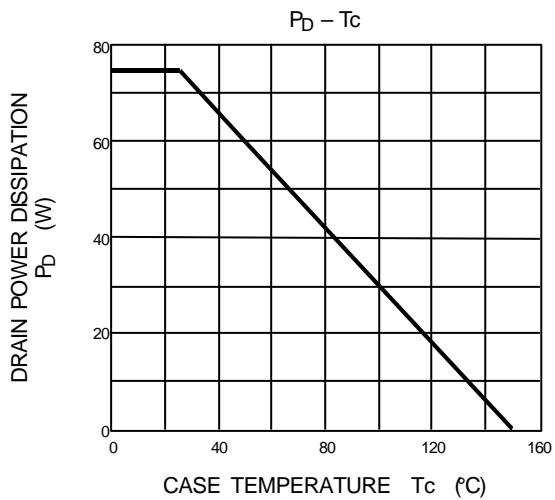
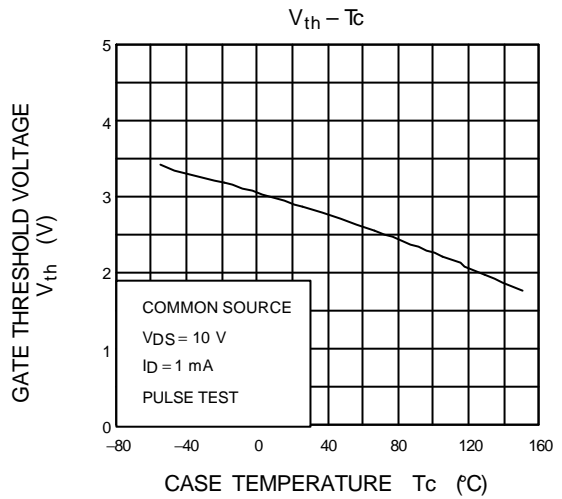
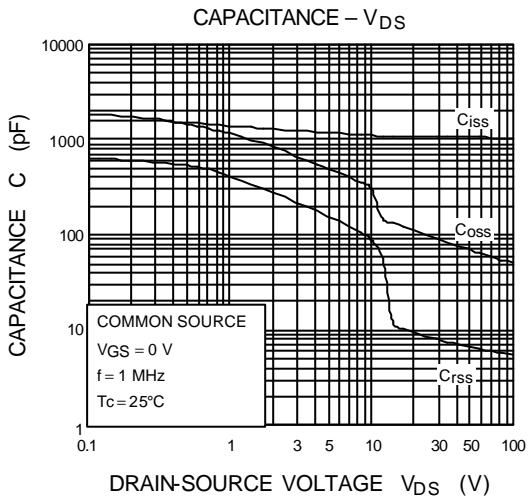
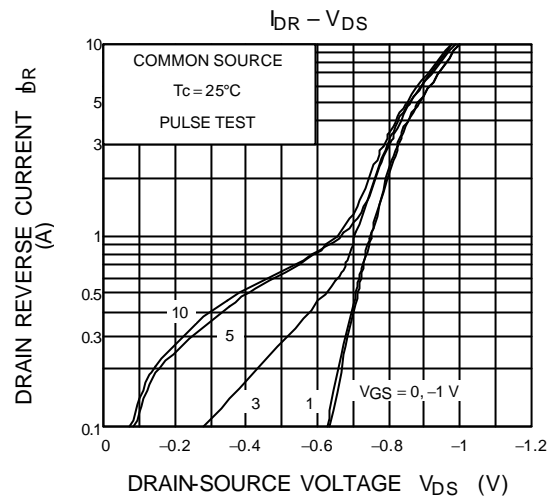
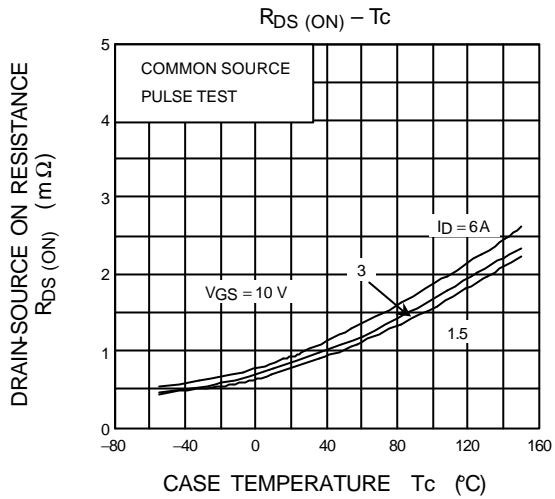
Source-Drain Ratings and Characteristics (Ta = 25°C)

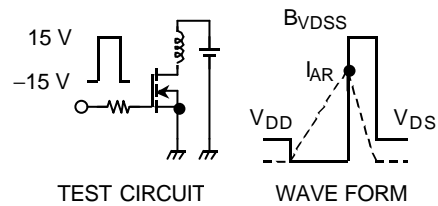
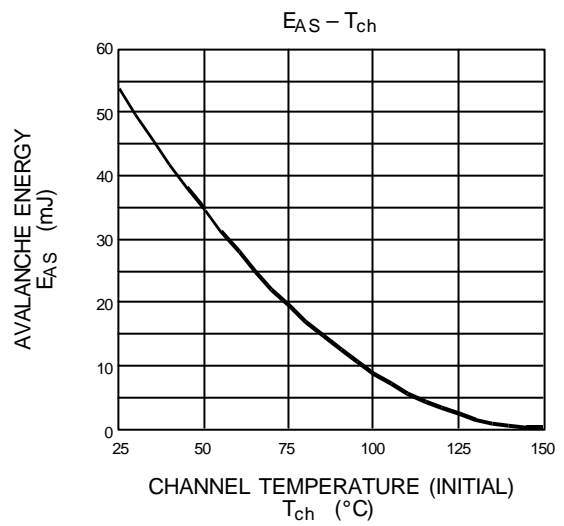
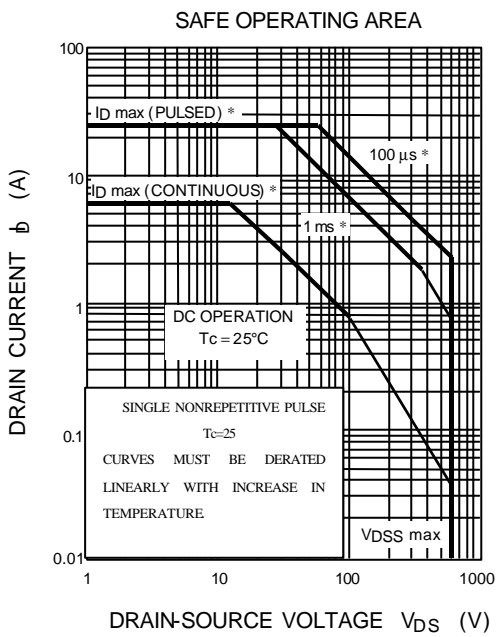
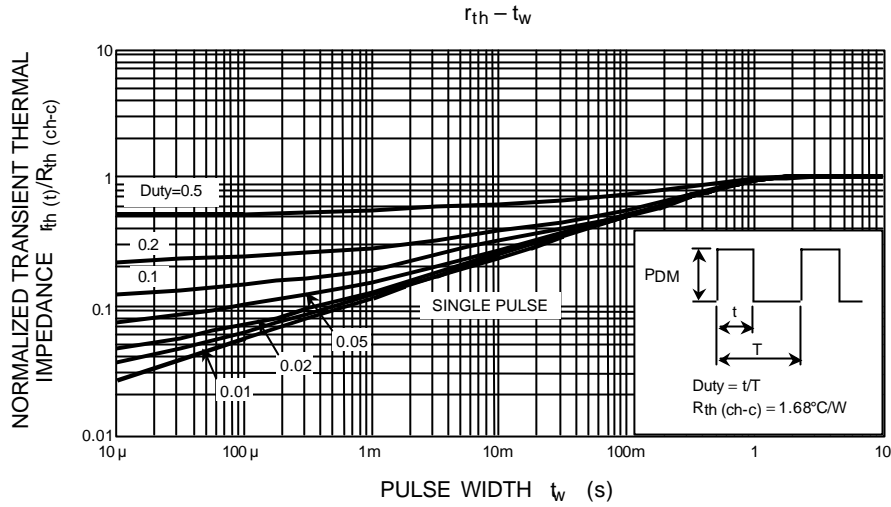
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)		I_{DR}	—	—	—	6	A
Pulse drain reverse current (Note 1)		I_{DRP}	—	—	—	24	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 6 A, V_{GS} = 0 V$	—	—	-1.7	V
Reverse recovery time		t_{rr}	$I_{DR} = 6 A, V_{GS} = 0 V,$	—	1000	—	ns
Reverse recovery charge		Q_{rr}	$dI_{DR}/dt = 100 A/\mu s$	—	7	—	μC

Marking









$R_G = 25 \Omega$
 $V_{DD} = 90 V, L = 2.6 mH$

$$\dot{A}_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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